74VCXH16240

Low-Voltage 1.8/2.5/3.3V 16-Bit Buffer

With 3.6 V–Tolerant Inputs and Outputs (3–State, Inverting)

The 74VCXH16240 is an advanced performance, inverting 16–bit buffer. It is designed for very high–speed, very low–power operation in 1.8 V, 2.5 V or 3.3 V systems.

When operating at 2.5 V (or 1.8 V) the part is designed to tolerate voltages it may encounter on either inputs or outputs when interfacing to 3.3 V busses. It is guaranteed to be over–voltage tolerant to 3.6 V.

The 74VCXH16240 is nibble controlled with each nibble functioning identically, but independently. The control pins may be tied together to obtain full 16–bit operation. The 3–state outputs are controlled by an Output Enable ($\overline{OEn}$) input for each nibble. When $\overline{OEn}$ is LOW, the outputs are on. When $\overline{OEn}$ is HIGH, the outputs are in the high impedance state. The data inputs include active bushold circuitry, eliminating the need for external pull–up resistors to hold unused or floating inputs at a valid logic state.

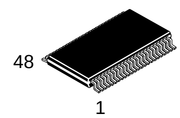
- Designed for Low Voltage Operation: V_{CC} = 1.65–3.6 V
- 3.6 V Tolerant Inputs and Outputs
- High Speed Operation: 2.5 ns max for 3.0 to 3.6 V
  3.0 ns max for 2.3 to 2.7 V
  6.0 ns max for 1.65 to 1.95 V
- Static Drive: ±24 mA Drive at 3.0 V
  ±18 mA Drive at 2.3 V
  ±6 mA Drive at 1.65 V
- Supports Live Insertion and Withdrawal
- Includes Active Bushold to Hold Unused or Floating Inputs at a Valid Logic State
- I_{OFF} Specification Guarantees High Impedance When V_{CC} = 0 V†
- Near Zero Static Supply Current in All Three Logic States (20 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds ±300mA @ 125°C
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V

†NOTE: To ensure the outputs activate in the 3–state condition, the output enable pins should be connected to V_{CC} through a pull–up resistor. The value of the resistor is determined by the current sinking capability of the output connected to the $\overline{OE}$ pin.

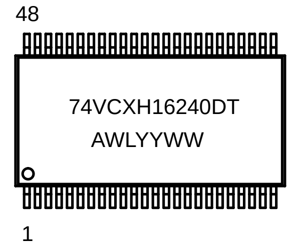
ON Semiconductor

http://onsemi.com

MARKING DIAGRAM



TSSOP–48
DT SUFFIX
CASE 1201



A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
74VCXH16240DT	TSSOP	39 / Rail
74VCXH16240DTR	TSSOP	2500 / Reel

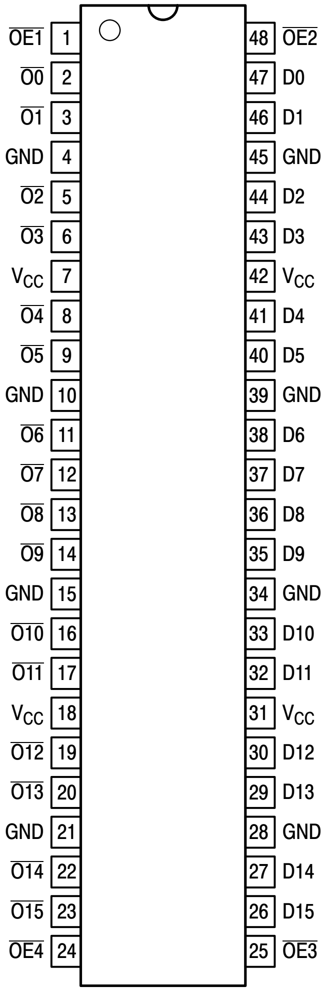


Figure 1. 48–Lead Pinout
(Top View)

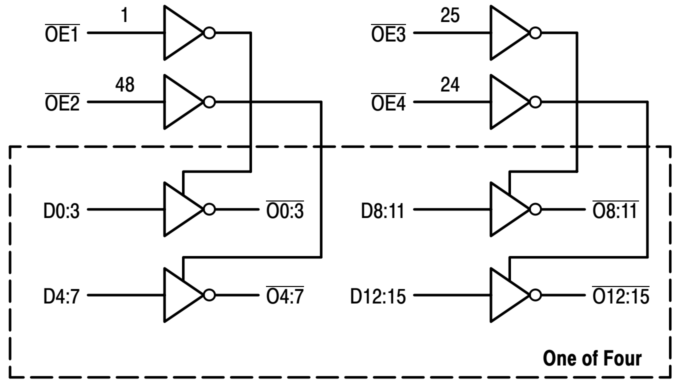
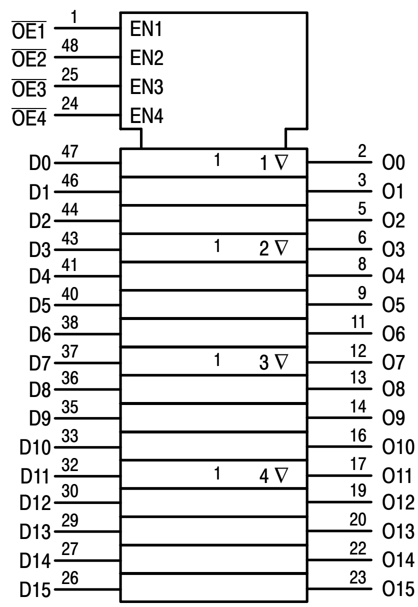


Figure 2. Logic Diagram



PIN NAMES

Pins	Function
$\overline{OEn}$	Output Enable Inputs
D0–D15	Inputs
O0–O15	Outputs

$\overline{OE1}$	D0:3	$\overline{O0:3}$	$\overline{OE2}$	D4:7	$\overline{O4:7}$	$\overline{OE3}$	D8:11	$\overline{O8:11}$	$\overline{OE4}$	D12:15	$\overline{O12:15}$
L	L	H	L	L	H	L	L	H	L	L	H
L	H	L	L	H	L	L	H	L	L	H	L
H	X	Z	H	X	Z	H	X	Z	H	X	Z

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions Are Acceptable, for I_{CC} reasons, DO NOT FLOAT Inputs

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V_{CC}	DC Supply Voltage	–0.5 to +4.6		V
V_I	DC Input Voltage	$-0.5 \le V_I \le +4.6$		V
V_O	DC Output Voltage	$-0.5 \le V_O \le +4.6$	Output in 3–State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Note 1.; Outputs Active	V
I_{IK}	DC Input Diode Current	–50	V_I < GND	mA
I_{OK}	DC Output Diode Current	–50	V_O < GND	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	±50		mA
I_{CC}	DC Supply Current Per Supply Pin	±100		mA
I_{GND}	DC Ground Current Per Ground Pin	±100		mA
T_{STG}	Storage Temperature Range	–65 to +150		°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit
V_{CC}	Supply Voltage Operating Data Retention Only	1.65 1.2	3.3 3.3	3.6 3.6	V
V_I	Input Voltage	–0.3		3.6	V
V_O	Output Voltage (Active State) (3–State)	0 0		V_{CC} 3.6	V
I_{OH}	HIGH Level Output Current, V_{CC} = 3.0V – 3.6V			–24	mA
I_{OL}	LOW Level Output Current, V_{CC} = 3.0V – 3.6V			24	mA
I_{OH}	HIGH Level Output Current, V_{CC} = 2.3V – 2.7V			–18	mA
I_{OL}	LOW Level Output Current, V_{CC} = 2.3V – 2.7V			18	mA
I_{OH}	HIGH Level Output Current, V_{CC} = 1.65 – 1.95V			–6	mA
I_{OL}	LOW Level Output Current, V_{CC} = 1.65 – 1.95V			6	mA
T_A	Operating Free–Air Temperature	–40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8V to 2.0V, V_{CC} = 3.0V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = –40°C to +85°C Min	Max	Unit
V_{IH}	HIGH Level Input Voltage (Note 2.)	1.65V ≤ V_{CC} < 2.3V	0.65 x V_{CC}		V
		2.3V ≤ V_{CC} ≤ 2.7V	1.6		
		2.7V < V_{CC} ≤ 3.6V	2.0		
V_{IL}	LOW Level Input Voltage (Note 2.)	1.65V ≤ V_{CC} < 2.3V		0.35 x V_{CC}	V
		2.3V ≤ V_{CC} ≤ 2.7V		0.7	
		2.7V < V_{CC} ≤ 3.6V		0.8	
V_{OH}	HIGH Level Output Voltage	1.65V ≤ V_{CC} ≤ 3.6V; I_{OH} = –100µA	V_{CC} – 0.2		V
		V_{CC} = 1.65V; I_{OH} = –6mA	1.25		
		V_{CC} = 2.3V; I_{OH} = –6mA	2.0		
		V_{CC} = 2.3V; I_{OH} = –12mA	1.8		
		V_{CC} = 2.3V; I_{OH} = –18mA	1.7		
		V_{CC} = 2.7V; I_{OH} = –12mA	2.2		
		V_{CC} = 3.0V; I_{OH} = –18mA	2.4		
		V_{CC} = 3.0V; I_{OH} = –24mA	2.2		
V_{OL}	LOW Level Output Voltage	1.65V ≤ V_{CC} ≤ 3.6V; I_{OL} = 100µA		0.2	V
		V_{CC} = 1.65V; I_{OL} = 6mA		0.3	
		V_{CC} = 2.3V; I_{OL} = 12mA		0.4	
		V_{CC} = 2.3V; I_{OL} = 18mA		0.6	
		V_{CC} = 2.7V; I_{OL} = 12mA		0.4	
		V_{CC} = 3.0V; I_{OL} = 18mA		0.4	
		V_{CC} = 3.0V; I_{OL} = 24mA		0.55	
I_I	Input Leakage Current	1.65V ≤ V_{CC} ≤ 3.6V; 0V ≤ V_I ≤ 3.6V		±5.0	µA
$I_{I(HOLD)}$	Minimum Bushold Input Current	V_{CC} = 3.0V, V_{IN} = 0.8V	75		µA
		V_{CC} = 3.0V, V_{IN} = 2.0V	–75		
		V_{CC} = 2.3V, V_{IN} = 0.7V	45		
		V_{CC} = 2.3V, V_{IN} = 1.6V	–45		
		V_{CC} = 1.65V, V_{IN} = 0.57V	25		
		V_{CC} = 1.65V, V_{IN} = 1.07V	–25		
$I_{I (OD)}$	Minimum Bushold Over–Drive Current Needed to Change State	V_{CC} = 3.6V, (Note 3.)	450		µA
		V_{CC} = 3.6V, (Note 4.)	–450		
		V_{CC} = 2.7V, (Note 3.)	300		
		V_{CC} = 2.7V, (Note 4.)	–300		
		V_{CC} = 1.95V, (Note 3.)	200		
		V_{CC} = 1.95V, (Note 4.)	–200		
I_{OZ}	3–State Output Current	1.65V ≤ V_{CC} ≤ 3.6V; 0V ≤ V_O ≤ 3.6V; V_I = V_{IH} or V_{IL}		±10	µA
I_{OFF}	Power–Off Leakage Current	V_{CC} = 0V; V_I or V_O = 3.6V		10	µA
I_{CC}	Quiescent Supply Current (Note 5.)	1.65V ≤ V_{CC} ≤ 3.6V; V_I = GND or V_{CC}		20	µA
		1.65V ≤ V_{CC} ≤ 3.6V; 3.6V ≤ V_I, V_O ≤ 3.6V		±20	µA
ΔI_{CC}	Increase in I_{CC} per Input	2.7V < V_{CC} ≤ 3.6V; V_{IH} = V_{CC} – 0.6V		750	µA

2. These values of V_I are used to test DC electrical characteristics only.
3. An external driver must source at least the specified current to switch from LOW–to–HIGH
4. An external driver must source at least the specified current to switch from HIGH–to–LOW
5. Outputs disabled or 3–state only.

AC CHARACTERISTICS (Note 6.; $t_R = t_F = 2.0ns$; $C_L = 30pF$; $R_L = 500\Omega$)

Symbol	Parameter	Waveform	Limits						Unit
			T_A = –40°C to +85°C						
			V_{CC} = 3.0V to 3.6V		V_{CC} = 2.3V to 2.7V		V_{CC} = 1.65 to 1.95V		
			Min	Max	Min	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay Input to Output	1	0.8 0.8	2.5 2.5	1.0 1.0	3.0 3.0	1.5 1.5	6.0 6.0	ns
t_{PZH} t_{PZL}	Output Enable Time to High and Low Level	2	0.8 0.8	3.5 3.5	1.0 1.0	4.1 4.1	1.5 1.5	8.2 8.2	ns
t_{PHZ} t_{PLZ}	Output Disable Time From High and Low Level	2	0.8 0.8	3.5 3.5	1.0 1.0	3.8 3.8	1.5 1.5	7.8 7.8	ns
t_{OSHL} t_{OSLH}	Output–to–Output Skew (Note 7.)			0.5 0.5		0.5 0.5		0.75 0.75	ns

6. For C_L = 50pF, add approximately 300ps to the AC maximum specification.
7. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t_{OSHL}) or LOW–to–HIGH (t_{OSLH}); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

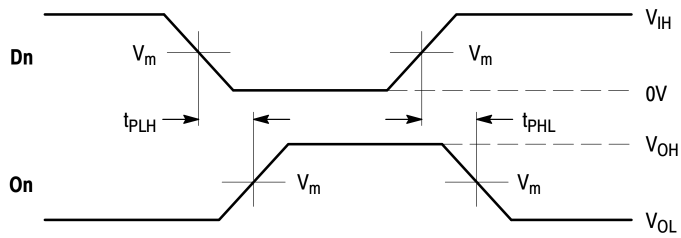
Symbol	Characteristic	Condition	T_A = +25°C	Unit
			Typ	
V_{OLP}	Dynamic LOW Peak Voltage (Note 8.)	V_{CC} = 1.8V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	0.25	V
		V_{CC} = 2.5V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	0.6	
		V_{CC} = 3.3V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	0.8	
V_{OLV}	Dynamic LOW Valley Voltage (Note 8.)	V_{CC} = 1.8V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	–0.25	V
		V_{CC} = 2.5V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	–0.6	
		V_{CC} = 3.3V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	–0.8	
V_{OHV}	Dynamic HIGH Valley Voltage (Note 9.)	V_{CC} = 1.8V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	1.5	V
		V_{CC} = 2.5V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	1.9	
		V_{CC} = 3.3V, C_L = 30pF, $V_{IH} = V_{CC}$, V_{IL} = 0V	2.2	

8. Number of outputs defined as “n”. Measured with “n–1” outputs switching from HIGH–to–LOW or LOW–to–HIGH. The remaining output is measured in the LOW state.
9. Number of outputs defined as “n”. Measured with “n–1” outputs switching from HIGH–to–LOW or LOW–to–HIGH. The remaining output is measured in the HIGH state.

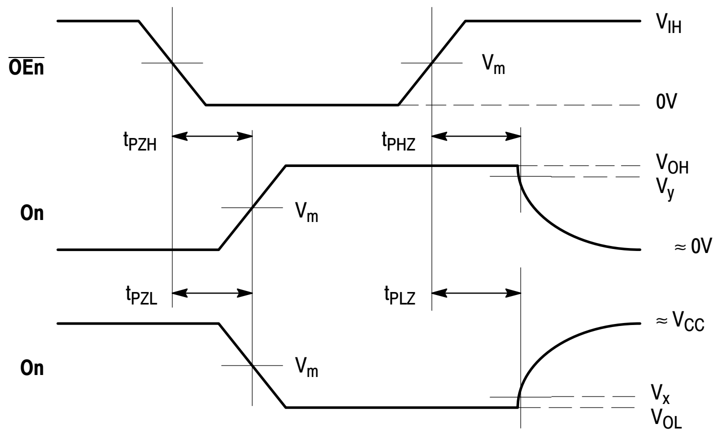
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	Note 10.	6	pF
C_{OUT}	Output Capacitance	Note 10.	7	pF
C_{PD}	Power Dissipation Capacitance	Note 10., 10MHz	20	pF

10. V_{CC} = 1.8, 2.5 or 3.3V; V_I = 0V or V_{CC}.



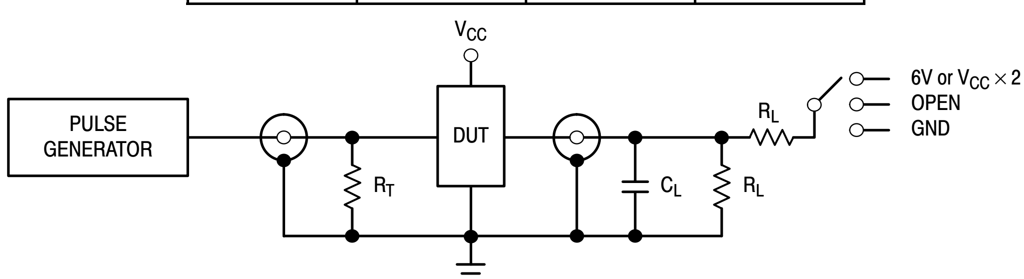
WAVEFORM 1 – PROPAGATION DELAYS
$t_R = t_F$ = 2.0ns, 10% to 90%; f = 1MHz; t_W = 500ns



WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES
$t_R = t_F$ = 2.0ns, 10% to 90%; f = 1MHz; t_W = 500ns

Figure 3. AC Waveforms

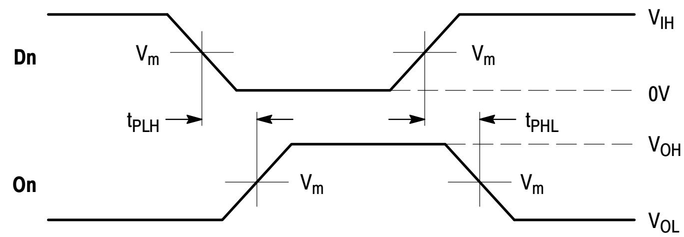
Symbol	V_{CC}		
	3.3V ±0.3V	**2.5V ±0.2V**	**1.8V ±0.15V**
V_{IH}	2.7V	V_{CC}	V_{CC}
V_m	1.5V	$V_{CC}/2$	$V_{CC}/2$
V_x	V_{OL} + 0.3V	V_{OL} + 0.15V	V_{OL} + 0.15V
V_y	V_{OH} – 0.3V	V_{OH} – 0.15V	V_{OH} – 0.15V



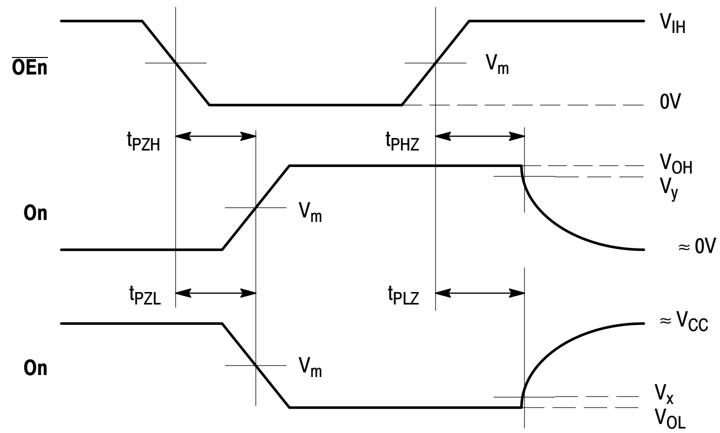
TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	6V at V_{CC} = 3.3 ±0.3V; $V_{CC} \times 2$ at V_{CC} = 2.5 ±0.2V; 1.8 ±0.15V
t_{PZH}, t_{PHZ}	GND

C_L = 30pF or equivalent (Includes jig and probe capacitance)
R_L = 500Ω or equivalent
R_T = Z_{OUT} of pulse generator (typically 50Ω)

Figure 4. Test Circuit



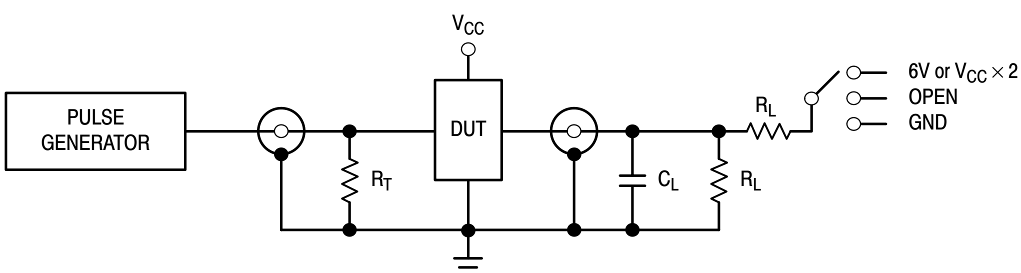
WAVEFORM 3 – PROPAGATION DELAYS
$t_R = t_F$ = 2.0ns, 10% to 90%; f = 1MHz; t_W = 500ns



WAVEFORM 4 – OUTPUT ENABLE AND DISABLE TIMES
$t_R = t_F$ = 2.0ns, 10% to 90%; f = 1MHz; t_W = 500ns

Figure 5. AC Waveforms

Symbol	V_{CC}	
	3.3V ±0.3V	**2.7V**
V_{IH}	2.7V	2.7V
V_m	1.5V	1.5V
V_x	V_{OL} + 0.3V	V_{OL} + 0.3V
V_y	V_{OH} – 0.3V	V_{OH} – 0.3V



TEST	SWITCH
t_{PLH}, t_{PHL}	Open
t_{PZL}, t_{PLZ}	6V at V_{CC} = 3.3 ±0.3V; $V_{CC} \times 2$ at V_{CC} = 2.5 ±0.2V; 1.8 ±0.15V
t_{PZH}, t_{PHZ}	GND

C_L = 50pF or equivalent (Includes jig and probe capacitance)
R_L = 500Ω or equivalent
R_T = Z_{OUT} of pulse generator (typically 50Ω)

Figure 6. Test Circuit

AC CHARACTERISTICS ($t_R = t_F$ = 2.0ns; C_L = 50pF; R_L = 500Ω)

Symbol	Parameter	Waveform	Limits				Unit
			T_A = –40°C to +85°C				
			V_{CC} = 3.0V to 3.6V		V_{CC} = 2.7V		
			Min	Max	Min	Max	
t_{PLH} t_{PHL}	Propagation Delay Input to Output	3	1.0 1.0	3.9 3.9		5.3 5.3	ns
t_{PZH} t_{PZL}	Output Enable Time to High and Low Level	4	1.0 1.0	5.0 5.0		6.1 6.1	ns
t_{PHZ} t_{PLZ}	Output Disable Time From High and Low Level	4	1.0 1.0	4.4 4.4		4.8 4.8	ns
t_{OSHL} t_{OSLH}	Output–to–Output Skew (Note 11.)			0.5 0.5		0.5 0.5	ns

11. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t_{OSHL}) or LOW–to–HIGH (t_{OSLH}); parameter guaranteed by design.

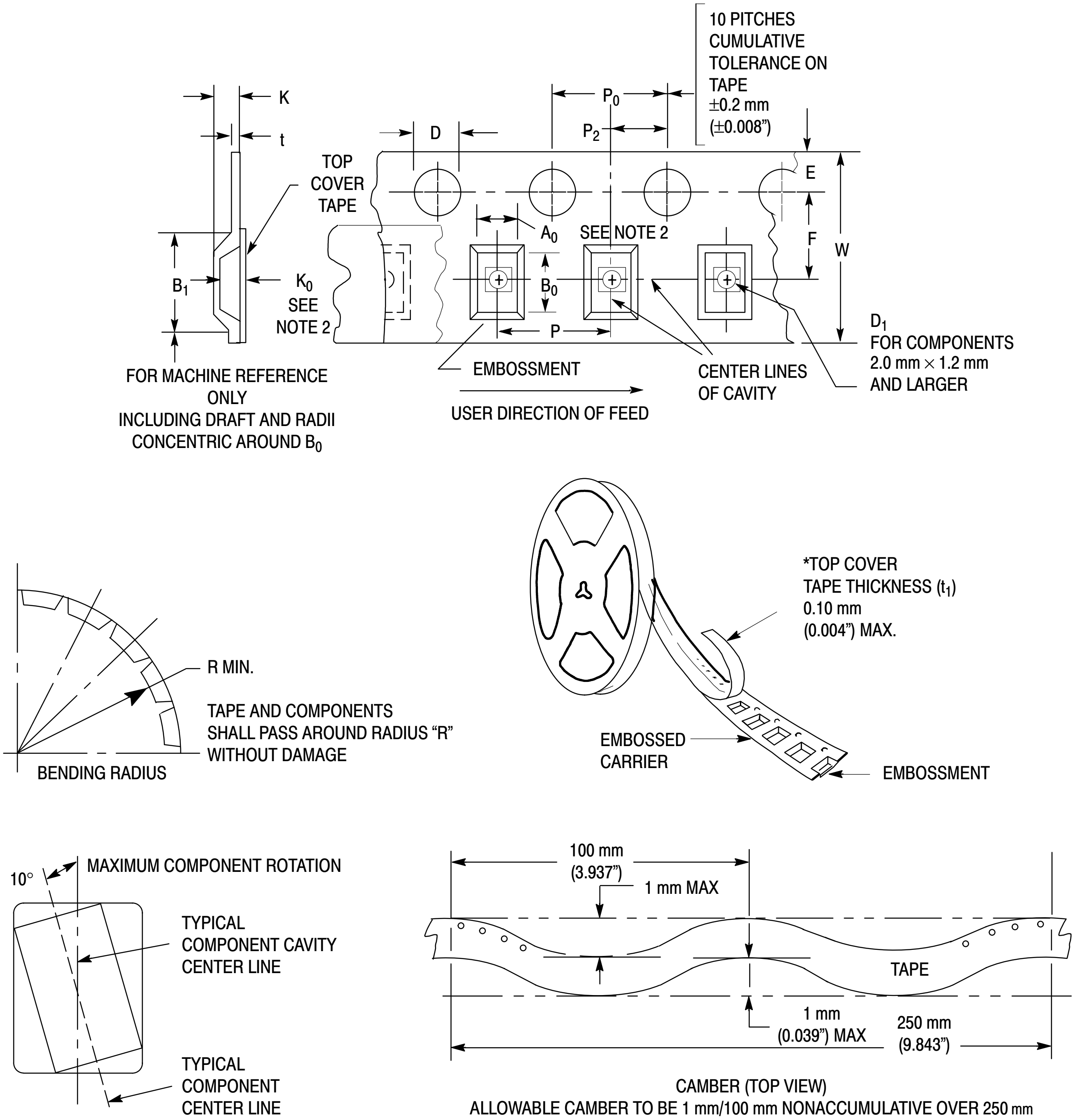


Figure 7. Carrier Tape Specifications

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Tape Size	B_1 Max	D	D_1	E	F	K	P	P_0	P_2	R	T	W
24mm	20.1mm (0.791")	1.5 + 0.1mm −0.0 (0.059 +0.004" −0.0)	1.5mm Min (0.060")	1.75 ±0.1 mm (0.069 ±0.004")	11.5 ±0.10 mm (0.453 ±0.004")	11.9 mm Max (0.468")	16.0 ±0.1 mm (0.63 ±0.004")	4.0 ±0.1 mm (0.157 ±0.004")	2.0 ±0.1 mm (0.079 ±0.004")	30 mm (1.18")	0.6 mm (0.024")	24.3 mm (0.957")

1. Metric Dimensions Govern–English are in parentheses for reference only.
2. A_0, B_0, and K_0 are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

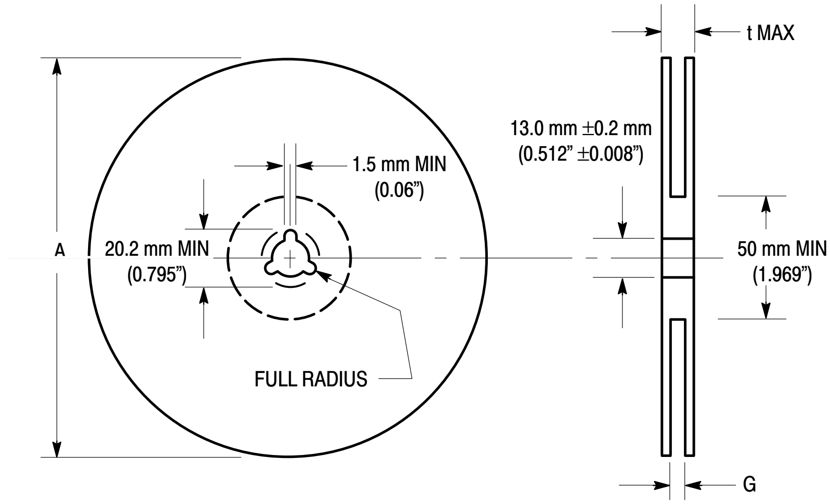


Figure 8. Reel Dimensions

REEL DIMENSIONS

Tape Size	A Max	G	t Max
24 mm	360 mm (14.173")	24.4 mm + 2.0 mm, −0.0 (0.961" + 0.078", −0.00)	30.4 mm (1.197")

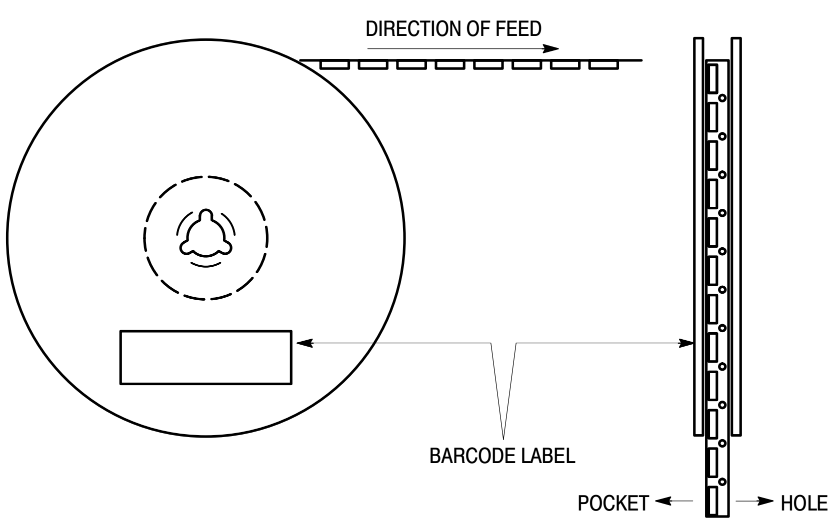


Figure 9. Reel Winding Direction

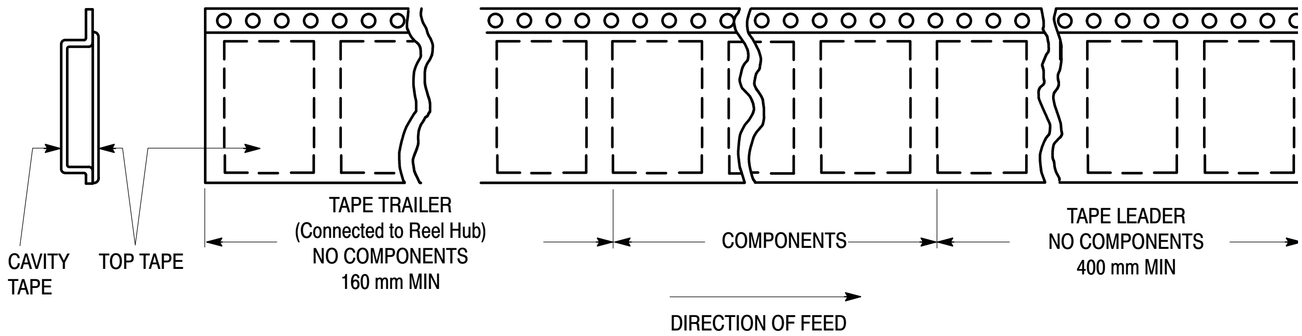


Figure 10. Tape Ends for Finished Goods

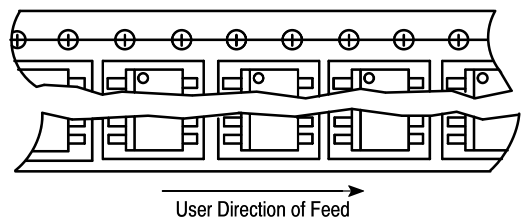
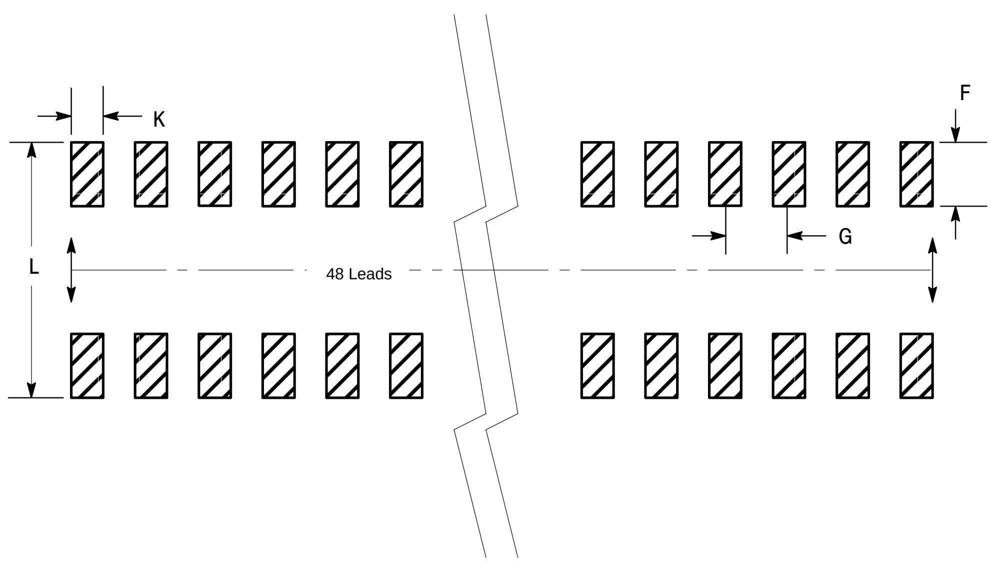


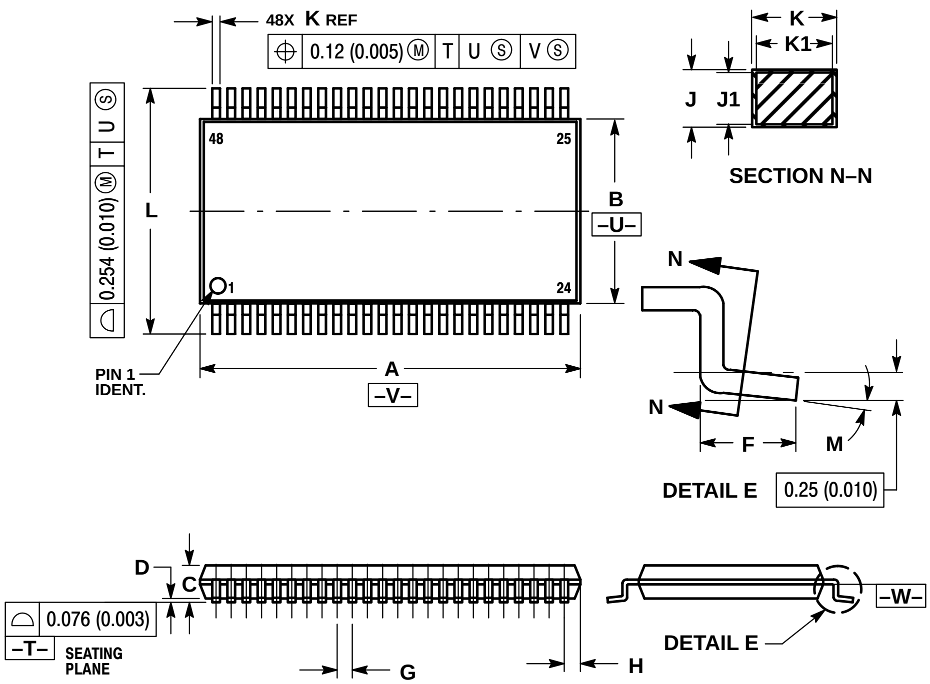
Figure 11. Reel Configuration



Package Footprint

PACKAGE DIMENSIONS

TSSOP
DT SUFFIX
CASE 1201–01
ISSUE A



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
6. DIMENSIONS A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	12.40	12.60	0.488	0.496
B	6.00	6.20	0.236	0.244
C	---	1.10	---	0.043
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.50 BSC		0.0197 BSC	
H	0.37	---	0.015	---
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.17	0.27	0.007	0.011
K1	0.17	0.23	0.007	0.009
L	7.95	8.25	0.313	0.325
M	0 °	8 °	0 °	8 °

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